

#8/Response  
8/27/02  
C. Lewis

S/N 09/387,164

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

Applicant: Yong-Jun Hu

Examiner: Sikha Roy

Serial No.: 09/387,164

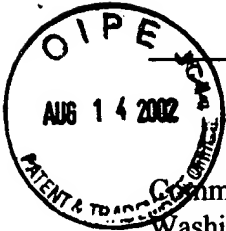
Group Art Unit: 2879

Filed: August 31, 1999

Docket: 303.607US1

Title: STRUCTURES AND METHODS TO ENHANCE FIELD EMISSION IN FIELD  
EMITTER DEVICES

RECEIVED  
PATENT  
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TECHNOLOGY CENTER 2800



**AMENDMENT AND RESPONSE UNDER 37 CFR § 1.111**

Commissioner for Patents  
Washington, D.C. 20231

Applicant has reviewed the Office Action mailed on May 9, 2002.

**IN THE CLAIMS**

None of the claims are amended, and no claims have been added or canceled, so that claims 1-36 remain pending in the Application per Applicant's previous Amendment and Response filed on February 12, 2002.

**REMARKS**

No claims have been amended, no claims have been canceled, and no new claims have been added. As a result, claims 1-36 remain pending in this Application.

**§102 Rejection of the Claims**

Claims 1-3, 5, 7, 9, 11, 13-26, and 33-35 were rejected under 35 U.S.C. § 102(b) as being anticipated by Doan et al. (U.S. Patent No. 5,372,973).

On page 2 of the latest Office Action, in describing Doan et al., the Examiner states that:

On the P-type silicon wafer is formed N-type conductivity regions or wells. The wells having been implanted with ions are the site of the emitter tips. The ion implantation is done by oxidation process, the oxidation phase being conducted sufficiently long to produce sideways growth of the resulting oxide layer and thus forming the emitter tips (column 4, lines 5-10) with ion implanted oxide layer.

However, upon closely reading Doan et al, all that can be said is that the "wells" are